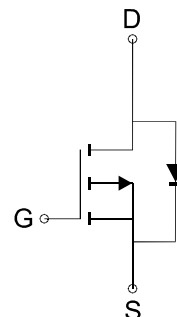
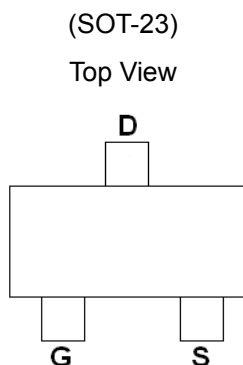


P-Channel 30V (D-S) MOSFET

GENERAL DESCRIPTION

The ME2345A is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where switching and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION



P-Channel MOSFET

FEATURES

- $R_{DS(ON)} \leq 68m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 80m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} \leq 100m\Omega @ V_{GS} = -2.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch
- DSC

Ordering Information: ME2345A (Pb-free)

ME2345A-G (Green product-Halogen free)

Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A = 25^\circ C$	I_D	-3.6	A
	$T_A = 70^\circ C$		-2.9	
Pulsed Drain Current		I_{DM}	-14	A
Maximum Power Dissipation	$T_A = 25^\circ C$	P_D	1.4	W
	$T_A = 70^\circ C$		0.9	
Operating Junction Temperature		T_J	-55 to 150	$^\circ C$
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	90	$^\circ C/W$

*The device mounted on 1in² FR4 board with 2 oz copper

P-Channel 30V (D-S) MOSFET

Electrical Characteristics (TA=25°C Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μ A	-0.6		-1.3	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = $\pm$ 12V			$\pm$ 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V			-1	μ A
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D = -4.2A		57	68	m Ω
		V _{GS} =-4.5V, I _D = -4A		62	80	
		V _{GS} =-2.5V, I _D = -2A		80	100	
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
DYNAMIC						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-4A		9		nC
Q _{gs}	Gate-Source Charge			2.3		
Q _{gd}	Gate-Drain Charge			2		
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		710		pF
C _{oss}	Output Capacitance			70		
C _{rss}	Reverse Transfer Capacitance			20		
t _{d(on)}	Turn-On Delay Time	V _{DS} =-15V, R _L =3.6 Ω R _{GEN} =6 Ω , V _{GS} =-10V		37		ns
t _r	Turn-On Rise Time			23		
t _{d(off)}	Turn-Off Delay Time			46		
t _f	Turn-Off Fall time			3		

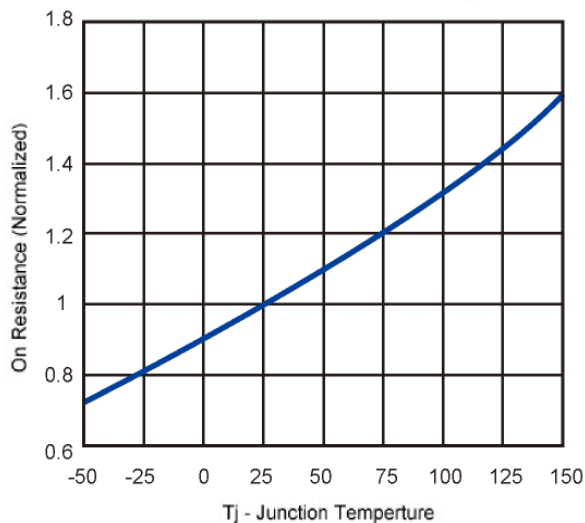
Notes: a. Pulse test: pulse width $\leq$ 300 μ s, duty cycle $\leq$ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

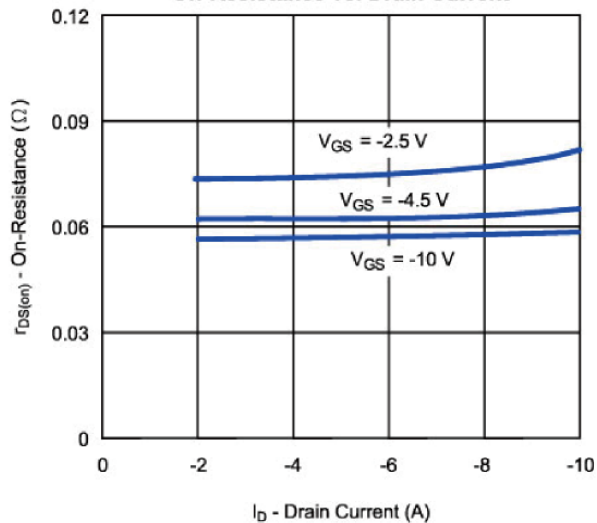
P-Channel 30V (D-S) MOSFET

Typical Characteristics (T_J = 25°C Noted)

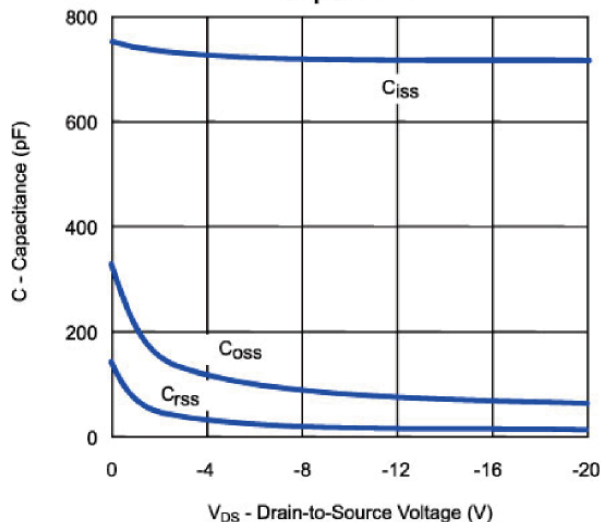
On Resistance vs. Junction Temperature



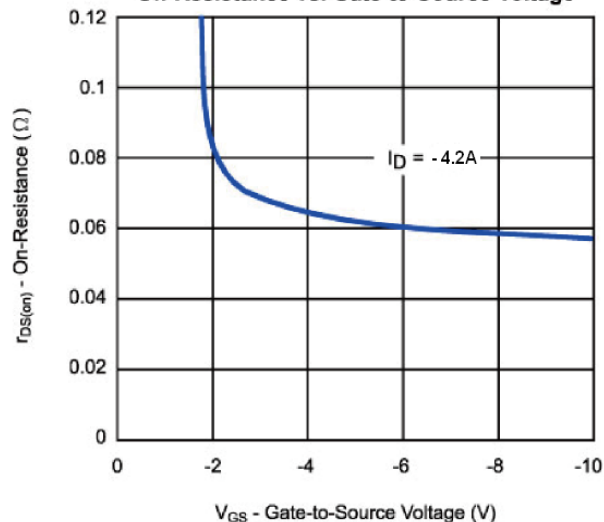
On-Resistance vs. Drain Current



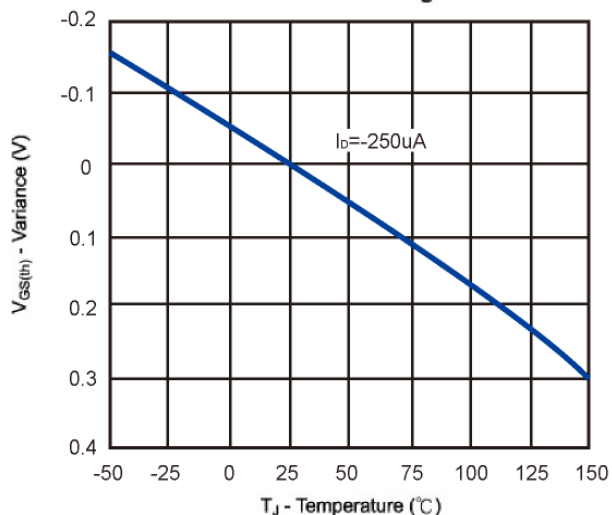
Capacitance



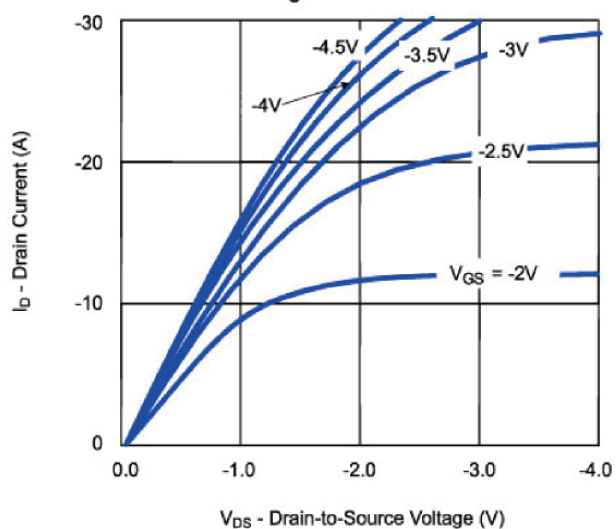
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

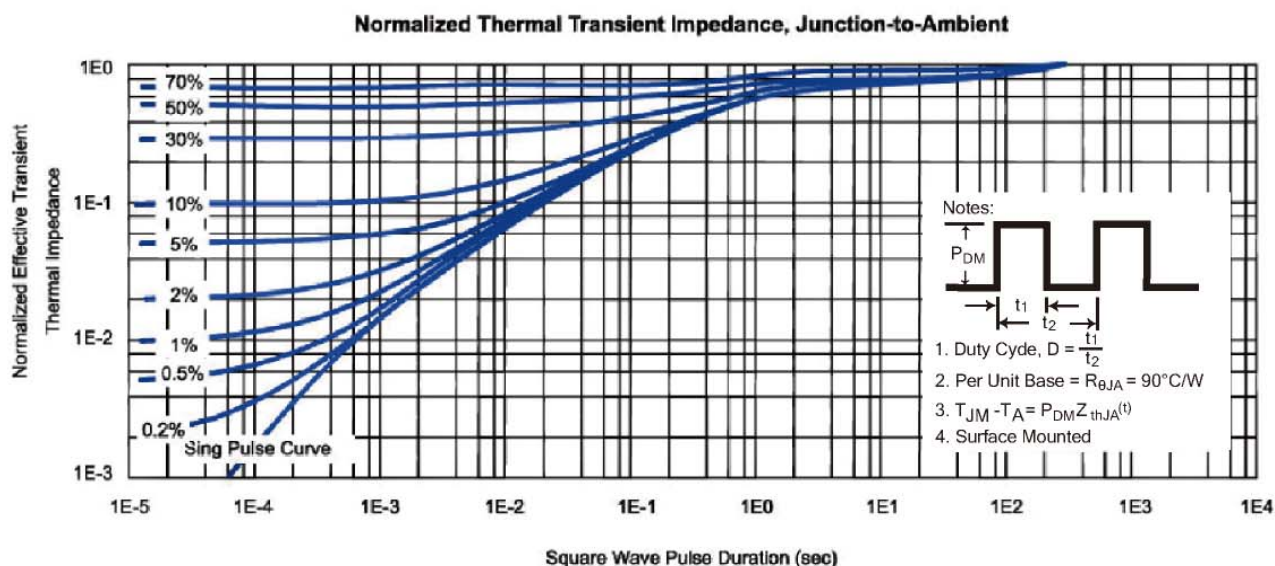
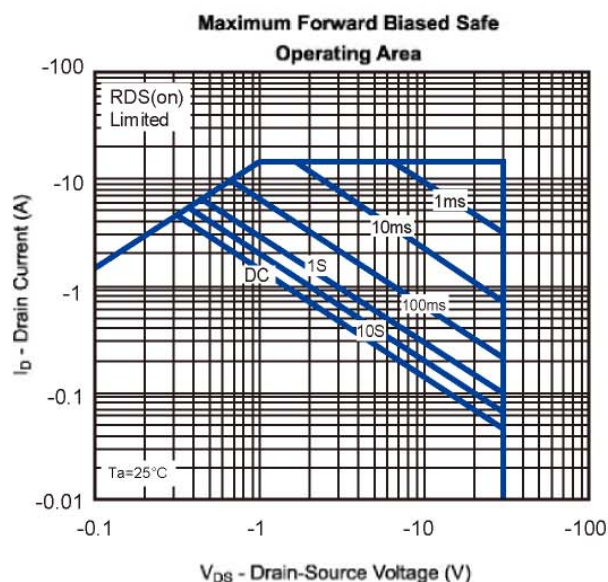
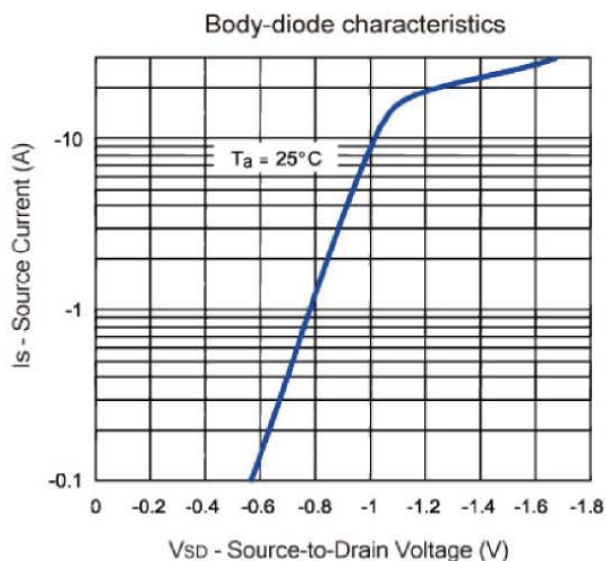
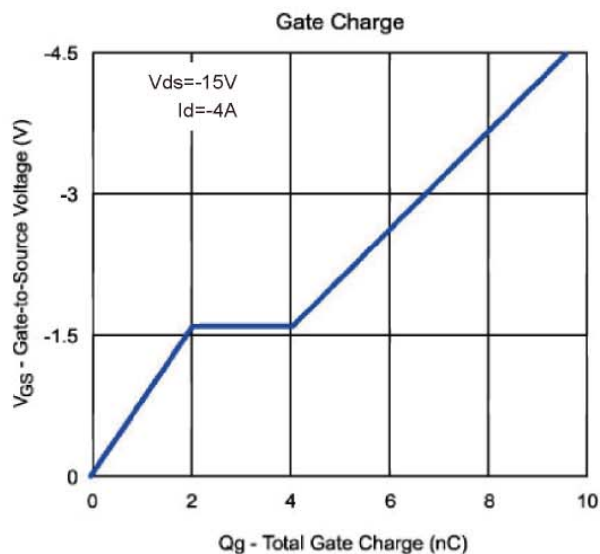


On-Region Characteristics

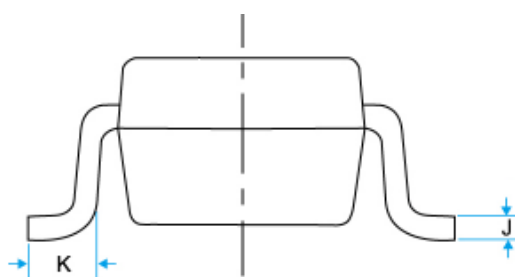
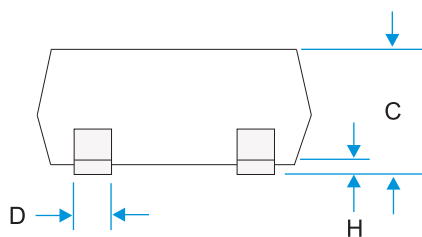
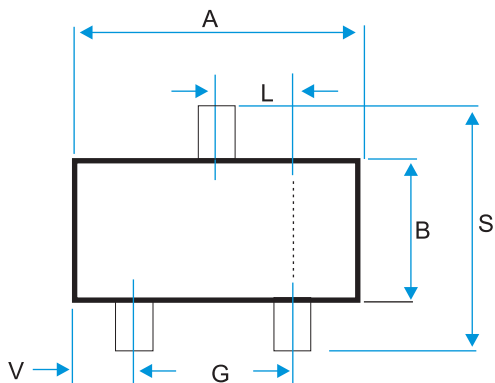


P-Channel 30V (D-S) MOSFET

Typical Characteristics ($T_J = 25^\circ\text{C}$ Noted)



SOT-23 Package Outline



DIM	MILLIMETERS (mm)	
	MIN	MAX
A	2.800	3.00
B	1.200	1.70
C	0.900	1.30
D	0.350	0.50
G	1.780	2.04
H	0.010	0.15
J	0.085	0.20
K	0.300	0.65
L	0.890	1.02
S	2.100	3.00
V	0.450	0.60